

823.0052USQ

- c3  
cont  
Sub A*
- (a) applying said sample to a deposited continuous thin film by either adsorption or directly to a surface of said deposited continuous thin film; and
- (b) analyzing said sample by light desorption/ionization mass spectroscopy.

*c4*

6. (Twice Amended) A method according to claim 1, wherein said deposited thin film is selected from the group consisting of: silicon, germanium, carbon, hydrogen and mixtures thereof.

*Sub A*

7. (Twice Amended) A method according to claim 1, wherein the material used as said deposited continuous thin film is selected using criteria selected from the group consisting of light reflection, optical absorption, species absorption, analyte adsorption, ambient adsorption, analyte drying, and combinations thereof.

*c5*

18. (Twice Amended) A method according to claim 17 wherein said sample is obtained from a separation means selected from at least one of the group consisting of: chemical, physical, and electrical separation means.

*Sub A*

19. (Twice Amended) A method according to claim 18 wherein said separation means is selected from at least one of the group consisting of: liquid chromatography, gas chromatography, deposited thin film chromatography, size exclusion chromatography, affinity chromatography, gel electrophoresis, capillary or micro-capillary electrophoresis, and blotting.

*c6*

66. (Amended) A method according to claim 1, wherein said deposited continuous thin film is deposited on a substrate selected from the group consisting of silicon, semiconductors, insulators, glasses, plastics, polymers, metals, ceramics, and combinations thereof.